Fuji Electric

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FMV13N60S1

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FUJI POWER MOSFET

Super J-MOS series

N-Channel enhancement mode power MOSFET

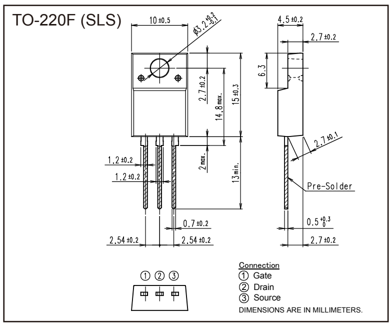
Features

Pb-free lead terminal
RoHS compliant

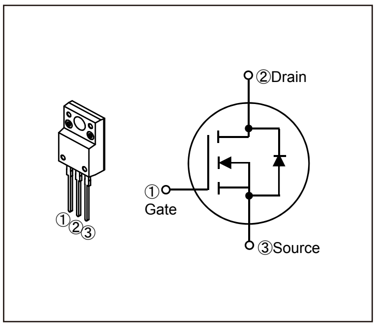
Applications

For switching

Outline Drawings [mm]



Equivalent circuit schematic



Absolute Maximum Ratings at T_C=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V_{DS}	600	V	
	V_{DSX}	600	V	V_{GS}=-30V
Continuous Drain Current	I_D	±13	A	Tc=25°C Note*1
		±8.2	A	Tc=100°C Note*1
Pulsed Drain Current	I_{DP}	±39	A	
Gate-Source Voltage	V_{GS}	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I_{AR}	3.4	A	Note *2
Non-Repetitive Maximum Avalanche Energy	E_{AS}	452.1	mJ	Note *3
Maximum Drain-Source dV/dt	dV_{DS}/dt	50	kV/μs	V_{DS}≤ 600V
Peak Diode Recovery dV/dt	dV/dt	15	kV/μs	Note *4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note *5
Maximum Power Dissipation	P_D	2.16	W	T_a=25°C
		43		T_C=25°C
Operating and Storage Temperature range	T_{ch}	150	°C	
	T_{stg}	-55 to +150	°C	
Isolation Voltage	V_{iso}	2	kVrms	t=60sec, f=60Hz

Note *1 : Limited by maximum channel temperature.
Note *2 : T_{ch}≤150°C, See Fig.1 and Fig.2
Note *3 : Starting T_{ch}=25°C, I_{AS}=2.1A, L=188mH, V_{DD}=60V, R_G=50Ω, See Fig.1 and Fig.2
E_{AS} limited by maximum channel temperature and avalanche current.
Note *4 : I_F≤-I_D, -di/dt=100A/μs, V_{DD}≤400V, V_{peak}≤BV_{DSS}, T_{ch}≤150°C.
Note *5 : I_F≤-I_D, dV/dt=15kV/μs, V_{DD}≤400V, V_{peak}≤BV_{DSS}, T_{ch}≤150°C.

Electrical Characteristics at T_C=25°C (unless otherwise specified)

• Static Ratings

Description	Symbol	Conditions		min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA V_{GS}=0V		600	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	I_D=250μA V_{DS}=V_{GS}		2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V V_{GS}=0V	T_{ch}=25°C	-	-	25	μA
		V_{DS}=480V V_{GS}=0V	T_{ch}=125°C	-	-	250	
Gate-Source Leakage Current	I_{GSS}	V_{GS}= ± 30V V_{DS}=0V		-	10	100	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	I_D=6.5A V_{GS}=10V		-	0.237	0.28	Ω
Gate resistance	R_G	f=1MHz, open drain		-	3.5	-	Ω

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• Dynamic Ratings

Description	Symbol	Conditions	min.	typ.	max.	Unit
Forward Transconductance	g_{fs}	I_D=6.5A V_{DS}=25V	6	12.5	-	S
Input Capacitance	C_{iss}	V_{DS}=10V V_{GS}=0V f=1MHz	-	1010	-	pF
Output Capacitance	C_{oss}		-	2160	-	
Reverse Transfer Capacitance	C_{rss}		-	200	-	
Effective output capacitance, energy related (Note *6)	$C_{o(er)}$	V_{GS}=0V V_{DS}=0…480V	-	70	-	
Effective output capacitance, time related (Note *7)	$C_{o(tr)}$	V_{GS}=0V V_{DS}=0…480V ID=constant	-	220	-	
Turn-On Time	$t_{d(on)}$	V_{DD}=400V, V_{GS}=10V/0V I_D=6.5A, R_G=24Ω See Fig.3 and Fig.4	-	13	-	ns
	t_r		-	38	-	
Turn-Off Time	$t_{d(off)}$		-	104	-	
	t_f		-	16	-	
Total Gate Charge	Q_G	V_{DD}=480V, I_D=13A V_{GS}=10V See Fig.5	-	35	-	nC
Gate-Source Charge	Q_{GS}		-	10	-	
Gate-Drain Charge	Q_{GD}		-	10.5	-	
Drain-Source crossover Charge	Q_{SW}		-	6.5	-	

Note *6 : $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% BV_{DSS}.
Note *7 : $C_{o(tr)}$ is a fixed capacitance that gives the same charging times as C_{oss} while V_{DS} is rising from 0 to 80% BV_{DSS}.

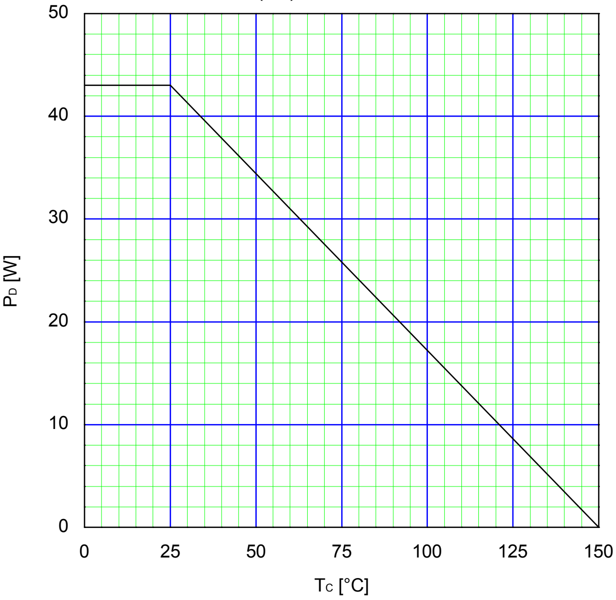
• Reverse Diode

Description	Symbol	Conditions	min.	typ.	max.	Unit
Avalanche Capability	I_{AV}	L=44.3mH, T_{ch}=25°C See Fig.1 and Fig.2	3.4	-	-	A
Diode Forward On-Voltage	V_{SD}	I_F=13A, V_{GS}=0V T_{ch}=25°C	-	0.9	1.35	V
Reverse Recovery Time	t_{rr}	I_F=13A, V_{DD}=400V -di/dt=100A/μs $V_{GS(Q1)}$=short, $V_{GS(Q2)}$=10V/0V R_G=330Ω T_{ch}=25°C See Fig.6 and Fig.7		330	-	ns
Reverse Recovery Charge	Q_{rr}		-	4.5	-	μC
Peak Reverse Recovery Current	I_{rp}		-	25	-	A

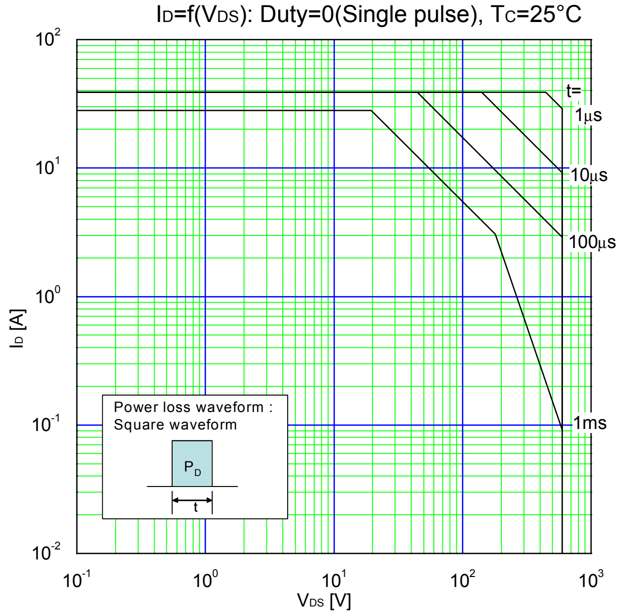
Thermal Resistance

Parameter	Symbol	min.	typ.	max.	Unit
Channel to Case	$R_{th(ch-c)}$	-	-	2.9	°C/W
Channel to Ambient	$R_{th(ch-a)}$	-	-	58	°C/W

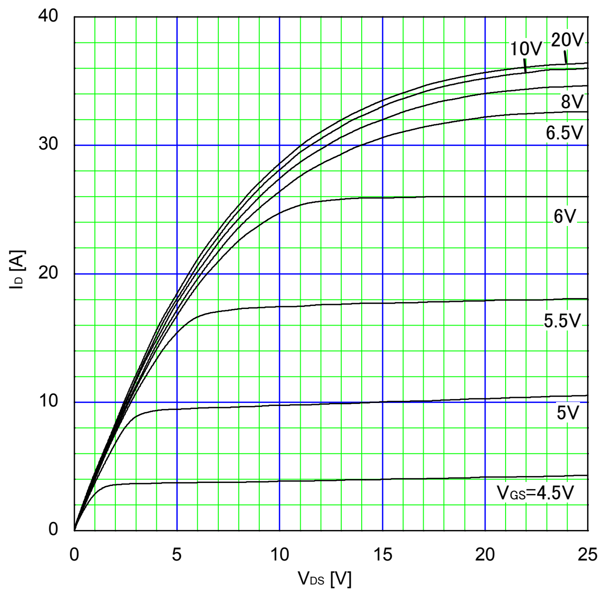
Allowable Power Dissipation
P_D= f(T_C)



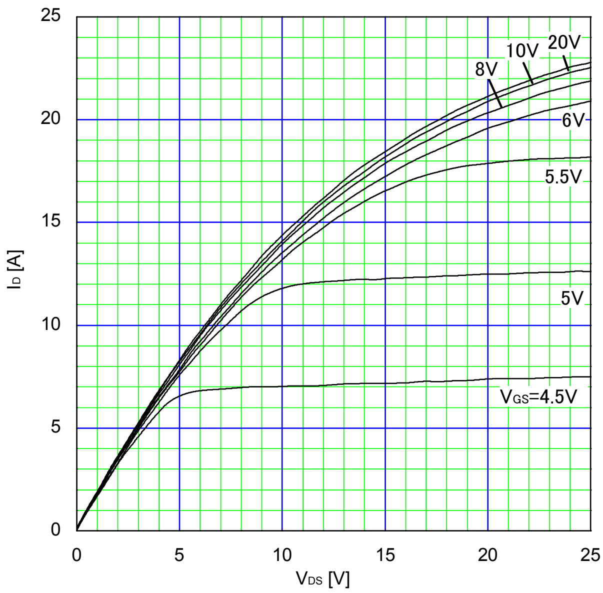
Safe Operating Area
I_D=f(V_{DS}): Duty=0(Single pulse), Tc=25°C



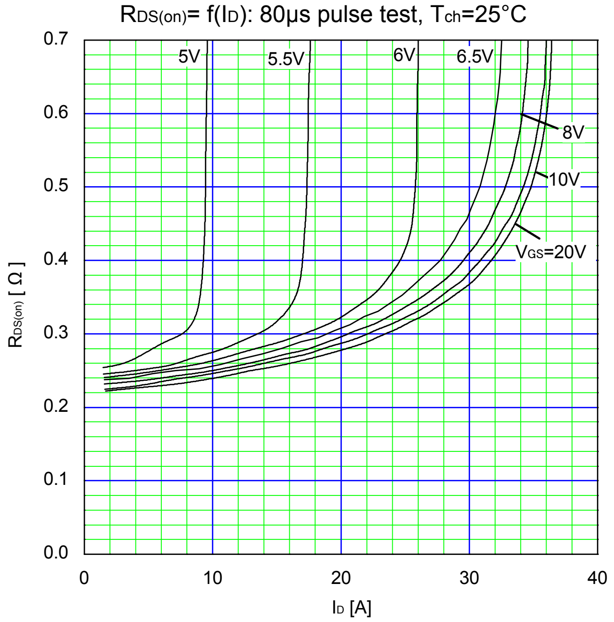
Typical Output Characteristics
I_D=f(V_{DS}): 80μs pulse test, T_{ch}=25°C



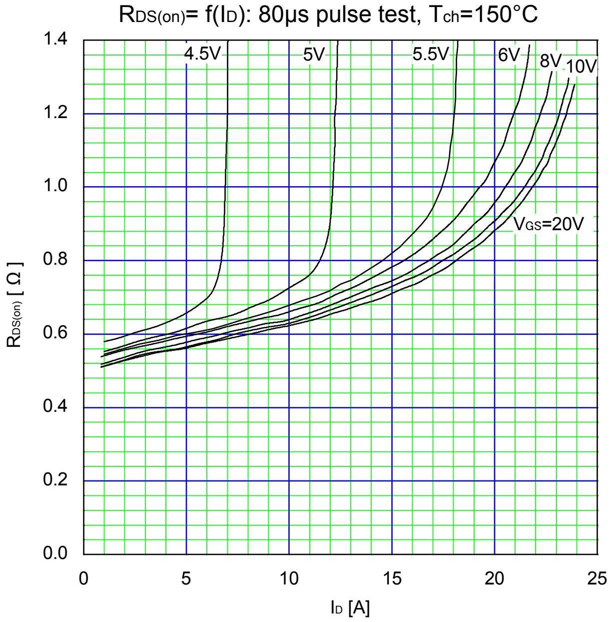
Typical Output Characteristics
I_D=f(V_{DS}): 80μs pulse test, T_{ch}=150°C



Typical Drain-Source on-state Resistance
$R_{DS(on)}$= f(I_D): 80μs pulse test, T_{ch}=25°C

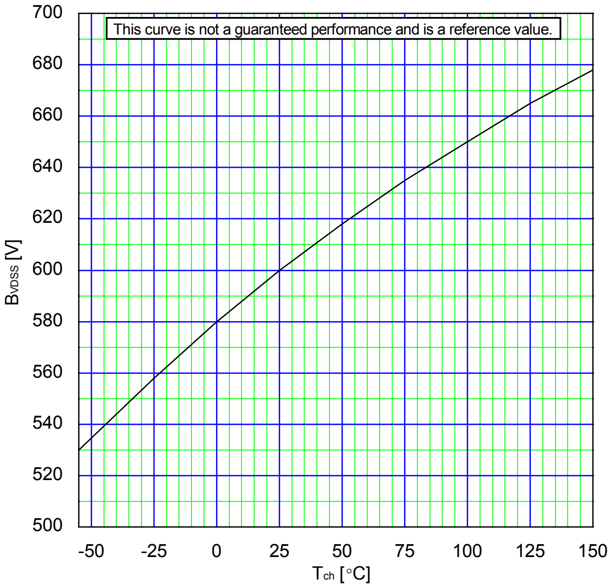


Typical Drain-Source on-state Resistance
$R_{DS(on)}$= f(I_D): 80μs pulse test, T_{ch}=150°C



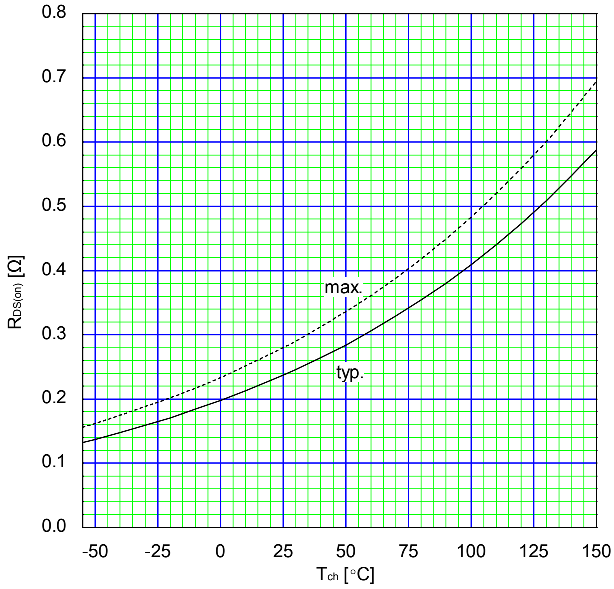
Drain-Source Breakdown Voltage

$BV_{DSS}=f(T_{ch}):I_D=10mA, V_{GS}=0V$



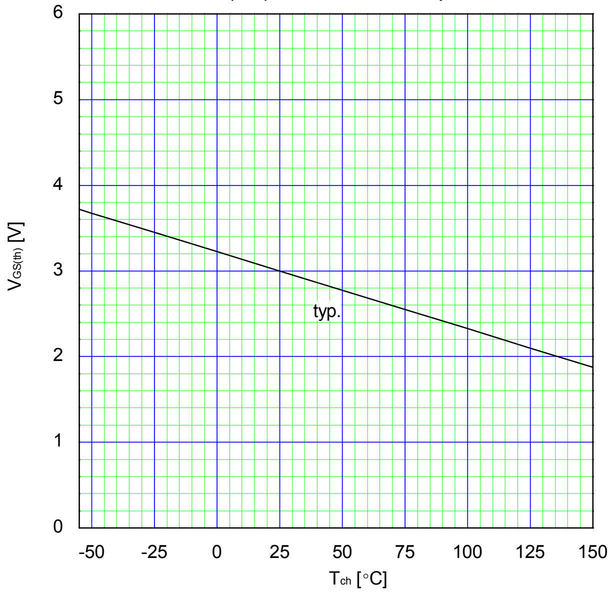
Drain-Source On-state Resistance

$R_{DS(on)}=f(T_{ch}):I_D=6.5A, V_{GS}=10V$



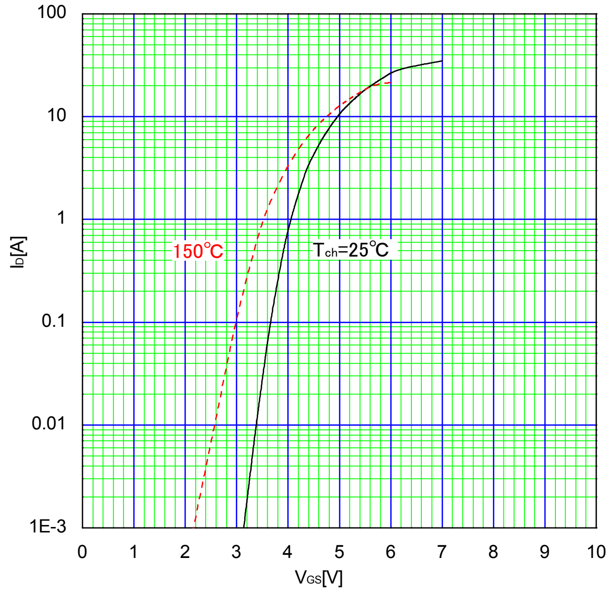
Gate Threshold Voltage vs. T_{ch}

$V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



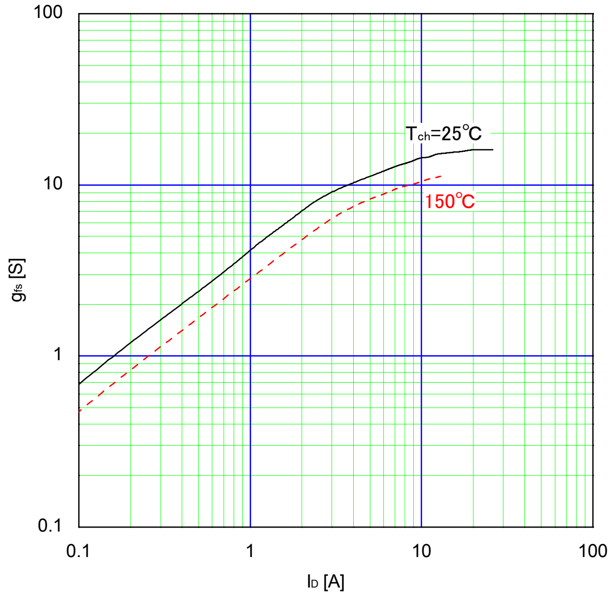
Typical Transfer Characteristic

$I_D=f(V_{GS})$:80µs pulse test, $V_{DS}=25V$



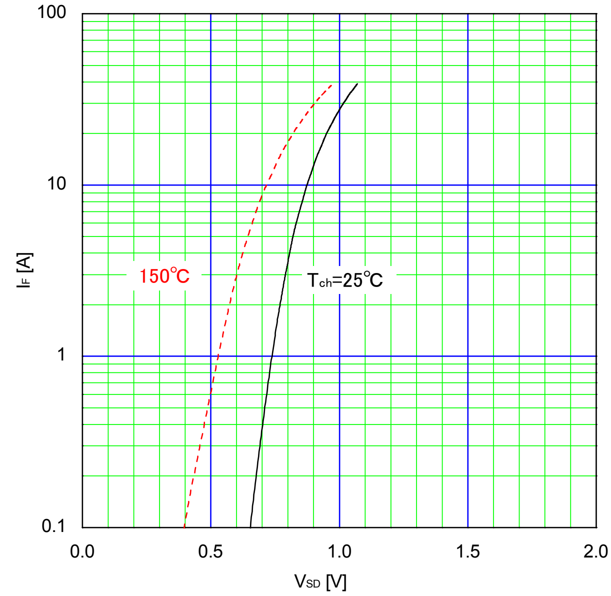
Typical Transconductance

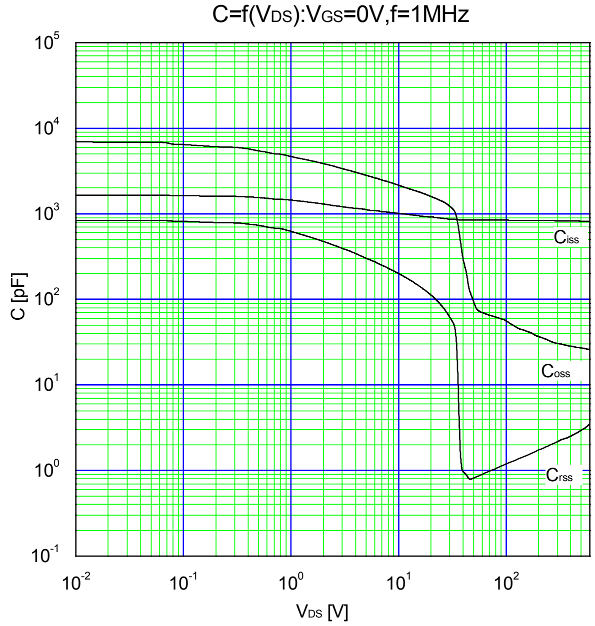
$g_{fs}=f(I_D)$:80µs pulse test, $V_{DS}=25V$

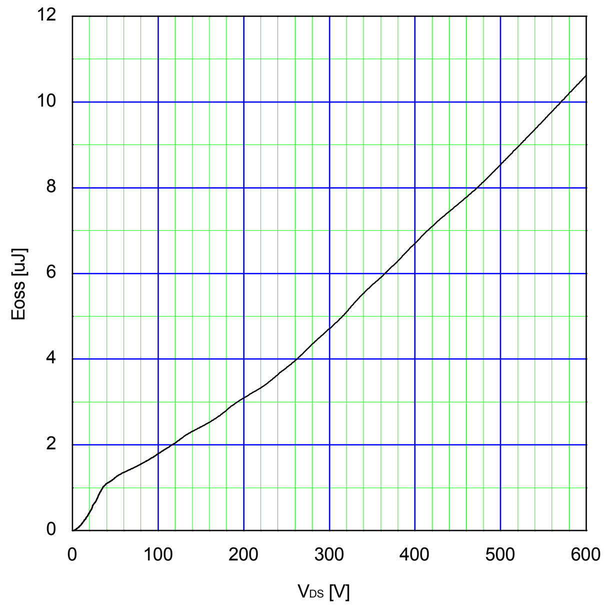


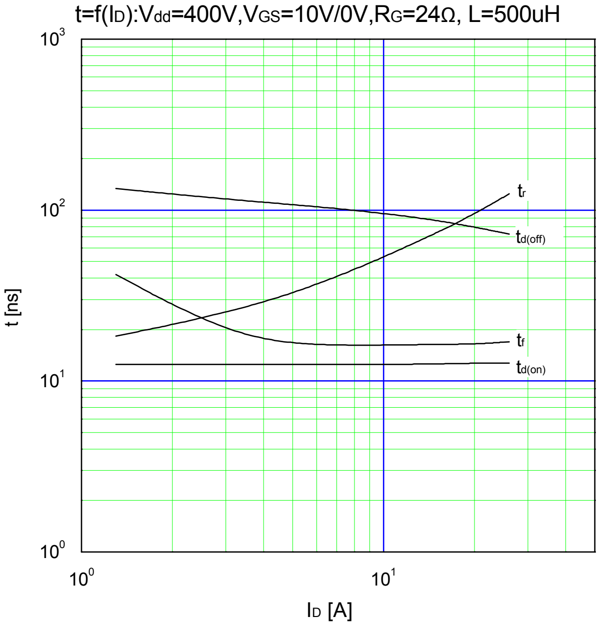
Typical Forward Characteristics of Reverse Diode

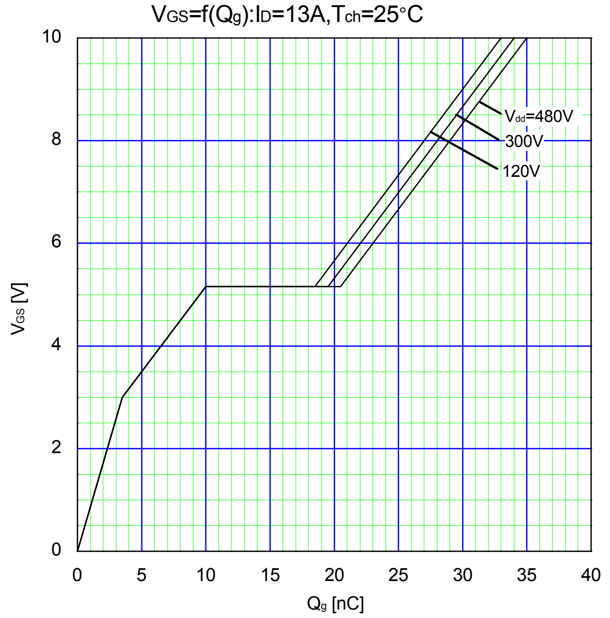
$I_F=f(V_{SD})$:80µs pulse test

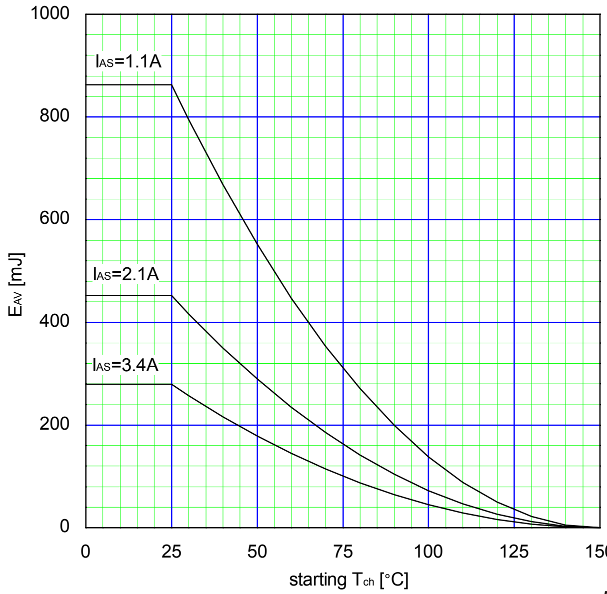


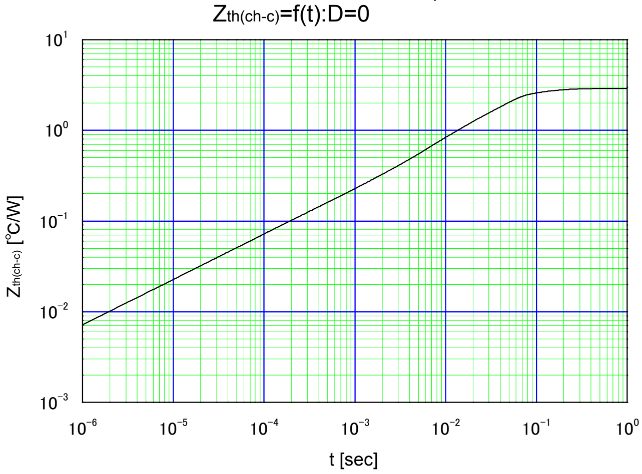

Typical Capacitance
C=f(VDS):VGS=0V,f=1MHz
C [pF]
VDS [V]
Ciss
Coss
Crss


Typical Coss stored energy
Eoss [uJ]
VDS [V]


Typical Switching Characteristics vs. ID Tch=25°C
t=f(ID):Vdd=400V,VGS=10V/0V,RG=24Ω, L=500uH
t [ns]
ID [A]
tr
td(off)
tf
td(on)


Typical Gate Charge Characteristics
VGS=f(Qg):ID=13A,Tch=25°C
VGS [V]
Qg [nC]
Vdd=480V
300V
120V


Maximum Avalanche Energy vs. startingTch
E(AV)=f(starting Tch):VCC=60V,I(AV)<=3.4A
EAV [mJ]
starting Tch [°C]
IAS=1.1A
IAS=2.1A
IAS=3.4A


Transient Thermal Impedance
Zth(ch-c)=f(t):D=0
Zth(ch-c) [°C/W]
t [sec]

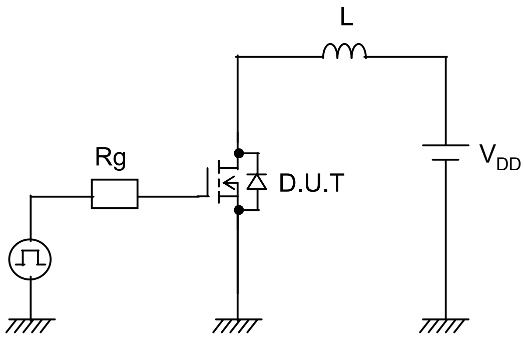


Fig.1 Avalanche Test circuit

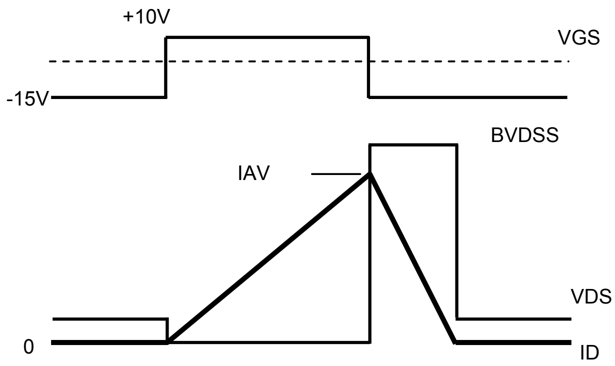


Fig.2 Operating waveforms of Avalanche Test

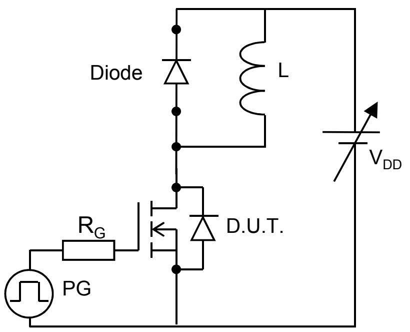


Fig.3 Switching Test circuit

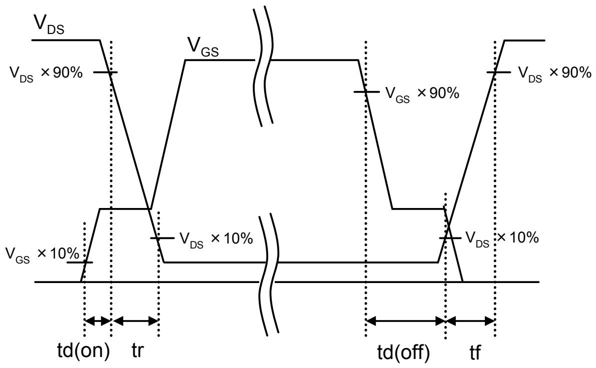


Fig.4 Operating waveform of Switching Test

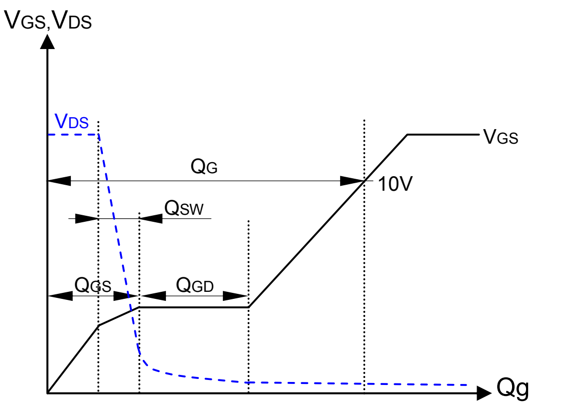


Fig.5 Operating waveform of Gate charge Test

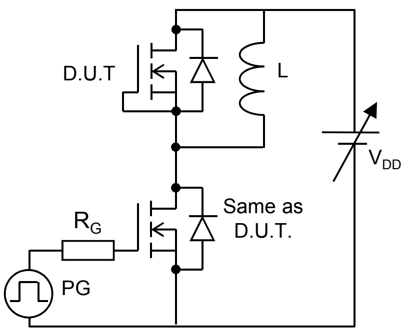


Fig.6 Reverse recovery Test circuit

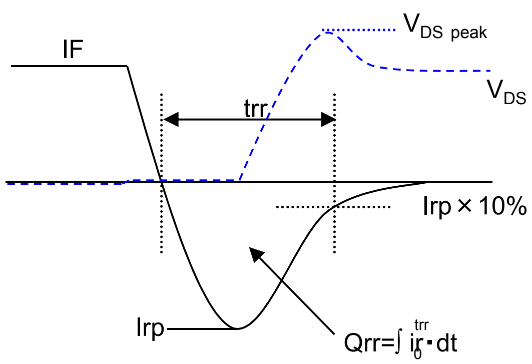
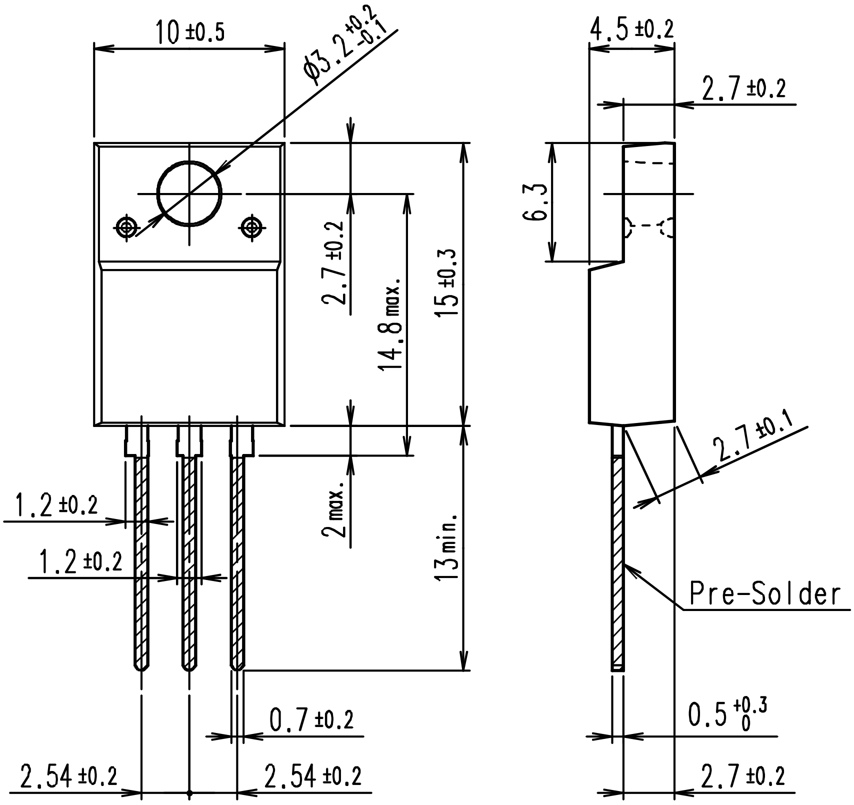
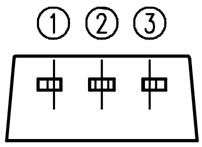


Fig.7 Operating waveform of Reverse recovery Test

Outview: TO-220F (SLS) Package

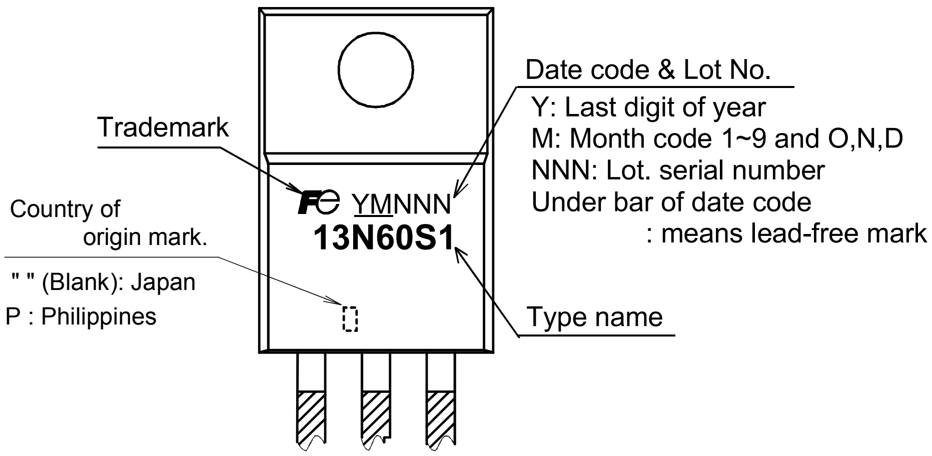




Connection
① Gate
② Drain
③ Source

DIMENSIONS ARE IN MILLIMETERS.

Marking



* The font (font type,size) and the trademark-size might be actually different.

WARNING

1. This Catalog contains the product specifications, characteristics, data, materials, and structures as of October 2015. The contents are subject to change without notice for specification changes or other reasons. When using a product listed in this Catalog, be sur to obtain the latest specifications.

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4. The products introduced in this Catalog are intended for use in the following electronic and electrical equipment which has normal reliability requirements.
   - Computers
   - OA equipment
   - Communications equipment (terminal devices)
   - Measurement equipment
   - Machine tools
   - Audiovisual equipment
   - Electrical home appliances
   - Personal equipment
   - Industrial robots etc.

5. If you need to use a product in this Catalog for equipment requiring higher reliability than normal, such as for the equipment listed below, it is imperative to contact Fuji Electric Co., Ltd. to obtain prior approval. When using these products for such equipment, take adequate measures such as a backup system to prevent the equipment from malfunctioning even if a Fuji's product incorporated in the equipment becomes faulty.
   - Transportation equipment (mounted on cars and ships)
   - Trunk communications equipment
   - Traffic-signal control equipment
   - Gas leakage detectors with an auto-shut-off feature
   - Emergency equipment for responding to disasters and anti-burglary devices
   - Safety devices
   - Medical equipment

6. Do not use products in this Catalog for the equipment requiring strict reliability such as the following and equivalents to strategic equipment (without limitation).
   - Space equipment
   - Aeronautic equipment
   - Nuclear control equipment
   - Submarine repeater equipment

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